

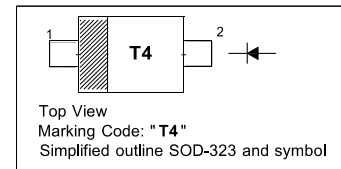
## BAS16WS Silicon Epitaxial Planar Switching Diode

### Features

- Fast switching diode

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	75	V
Peak Reverse Voltage	$V_{RM}$	100	V
Forward Current (Continuous)	$I_F$	250	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	0.5 1 2	A
		at $t = 1\text{ s}$	
		at $t = 1\text{ ms}$	
		at $t = 1\text{ }\mu\text{s}$	
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage	$V_F$	0.715	V
at $I_F = 1\text{ mA}$		0.855	
at $I_F = 10\text{ mA}$		1	
at $I_F = 50\text{ mA}$		1.25	
Reverse Leakage Current	$I_R$	1	$\mu\text{A}$
at $V_R = 75\text{ V}$		30	
at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$		50	
Diode Capacitance	$C_{tot}$	2	pF
at $V_R = 0\text{ V}, f = 1\text{ MHz}$			
Reverse Recovery Time	$t_{rr}$	6	ns
at $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$			

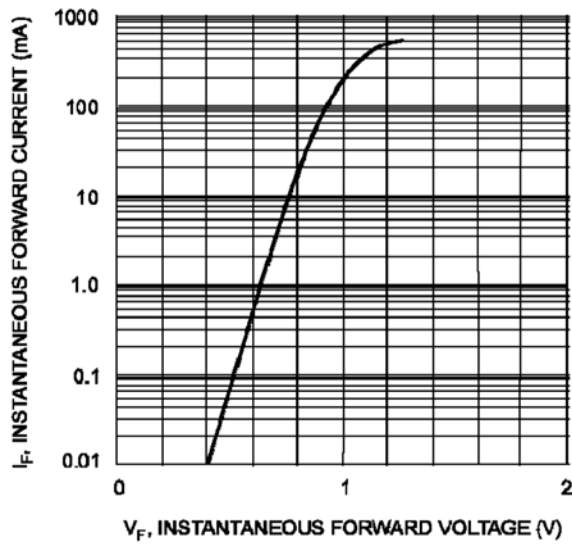


Fig. 1 Forward Characteristics

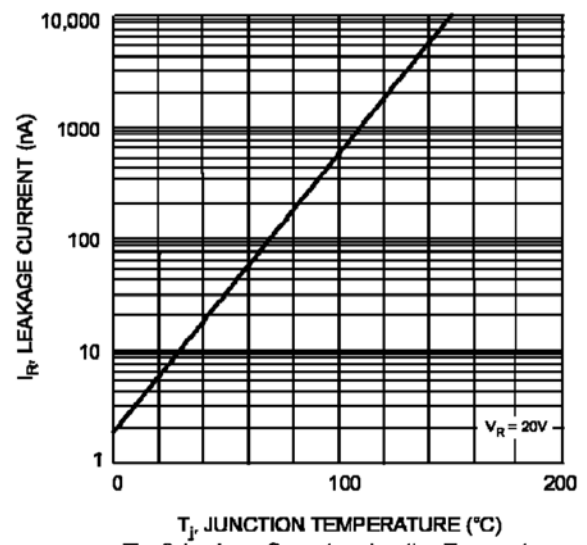


Fig. 2 Leakage Current vs Junction Temperature

## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

